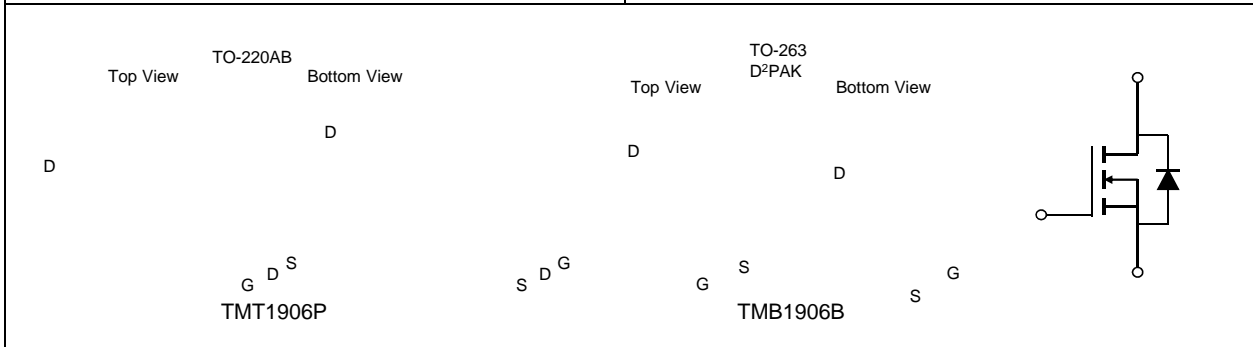


TMT1906P / TMB1906B N-CHANNEL POWER MOSFET

- Power Management for Inverter Systems.
- 60V / 120 A,
 $R_{DS(ON)} = 6.0 \text{ m}\Omega$ (typ.) @ $V_{GS} = 10\text{V}$
- Avalanche Rated
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)



Absolute Maximum Ratings

Symbol	Parameter	Rating	Unit
Common Ratings ($T_C = 25^\circ\text{C}$ Unless Otherwise Noted)			
V_{DSS}	Drain-Source Voltage	60	V
V_{GSS}	Gate-Source Voltage	± 25	
T_J	Maximum Junction Temperature	175	$^\circ\text{C}$
T_{STG}	Storage Temperature Range	-55 to 175	$^\circ\text{C}$
I_S	Diode Continuous Forward Current	$T_C = 25^\circ\text{C}$ 120	A
Mounted on Large Heat Sink			
I_{DM}	Pulsed Drain Current *	$T_C = 25^\circ\text{C}$ 380**	A
I_D	Continuous Drain Current	$T_C = 25^\circ\text{C}$ 120	A
		$T_C = 100^\circ\text{C}$ 80	
P_D	Maximum Power Dissipation	$T_C = 25^\circ\text{C}$ 188	W
		$T_C = 100^\circ\text{C}$ 94	
$R_{\theta JC}$	Thermal Resistance-Junction to Case	0.8	$^\circ\text{C/W}$
$R_{\theta JA}$	Thermal Resistance-Junction to Ambient	62.5	
Avalanche Ratings			
E_{AS}	Avalanche Energy, Single Pulsed	$L = 0.5\text{mH}$ 600***	mJ

Note : * Repetitive rating ; pulse width limited by junction temperature
 ** Drain current is limited by junction temperature
 *** $V_D = 48\text{V}$

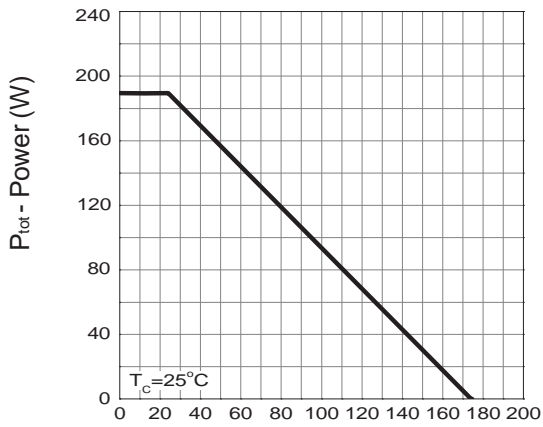
Electrical Characteristics (T_c = 25°C Unless Otherwise Noted)

Symbol	Parameter	Test Conditions	1906			Unit
			Min.	Typ.	Max.	
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =60V, V _{GS} =0V	-	-	1	μA
		T _J =85°C	-	-	10	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	2	3	4	V
I _{GSS}	Gate Leakage Current	V _{GS} =±25V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)*}	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =60A	-	6.0	7.5	mΩ
Diode Characteristics						
V _{SD*}	Diode Forward Voltage	I _{SD} =60A, V _{GS} =0V	-	0.8	1.2	V
t _{rr}	Reverse Recovery Time	I _{SD} =60A, di _{SD} /dt=100A/μs	-	50	-	ns
Q _{rr}	Reverse Recovery Charge		-	95	-	nC
Dynamic Characteristics						
R _G	Gate Resistance	V _{GS} =0V, V _{DS} =0V, F=1MHz	-	1.0	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =25V, Frequency=1.0MHz	-	4577	-	pF
C _{oss}	Output Capacitance		-	876	-	
C _{riss}	Reverse Transfer Capacitance		-	276	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _G =6Ω, I _{DS} =60A, V _{GS} =10V,	-	13	26	ns
T _r	Turn-on Rise Time		-	11	20	
t _{d(OFF)}	Turn-off Delay Time		-	40	66	
T _f	Turn-off Fall Time		-	60	95	
Gate Charge Characteristics^b						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =60A	-	96	-	nC
Q _{gs}	Gate-Source Charge		-	21	-	
Q _{gd}	Gate-Drain Charge		-	23	-	

Note * : Pulse test ; pulse width ≤300μs, duty cycle ≤2%.

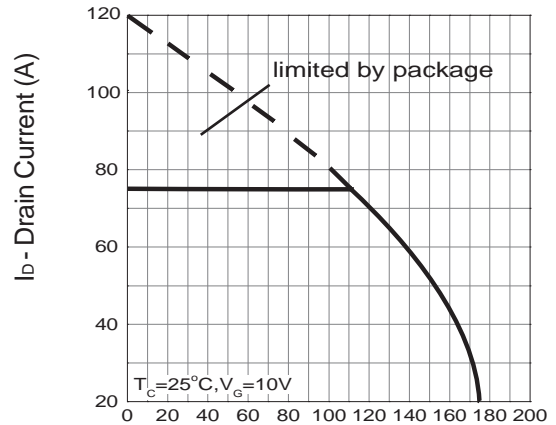
Typical Operating Characteristics

Power Dissipation



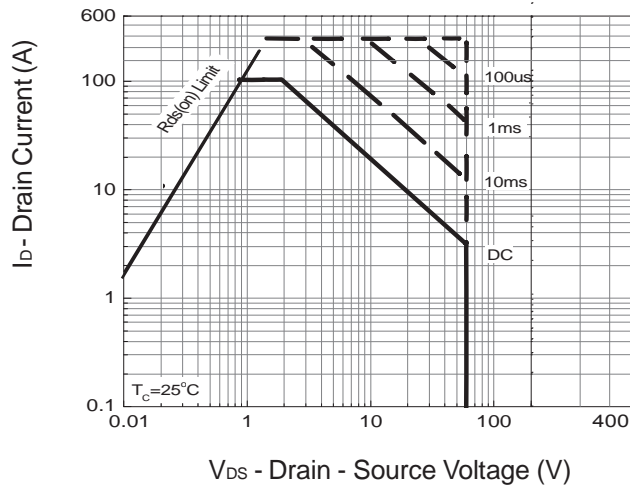
T_c - Case Temperature (°C)

Drain Current



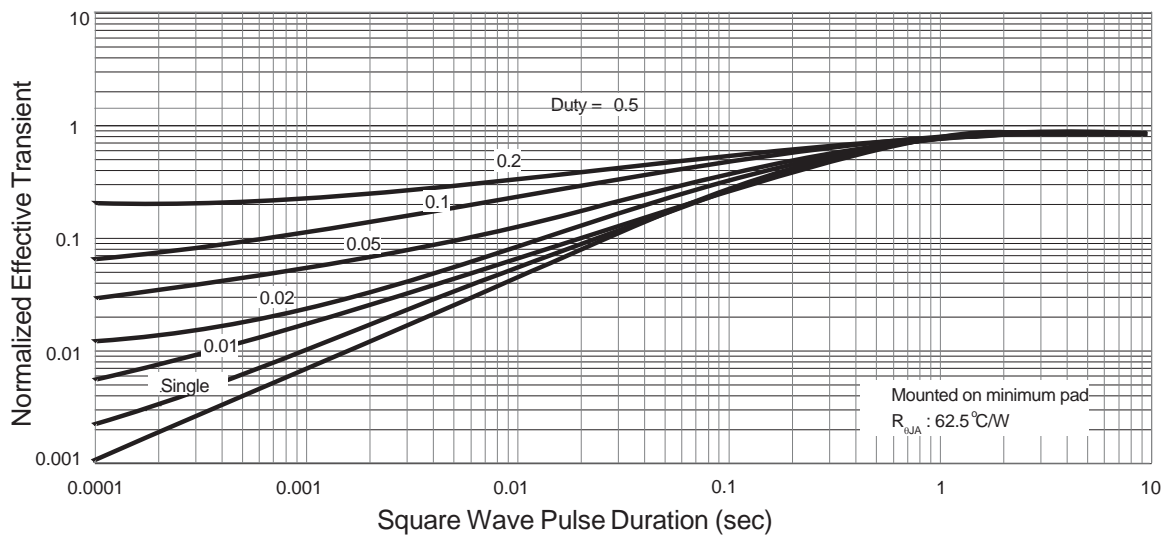
T_c - Case Temperature (°C)

Safe Operation Area



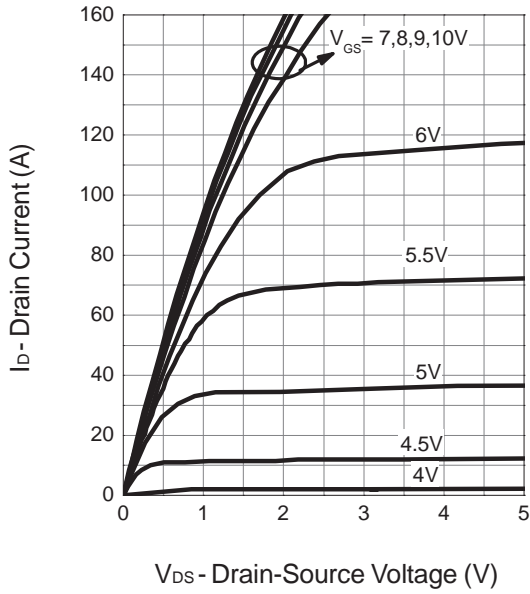
V_{DS} - Drain - Source Voltage (V)

Thermal Transient Impedance

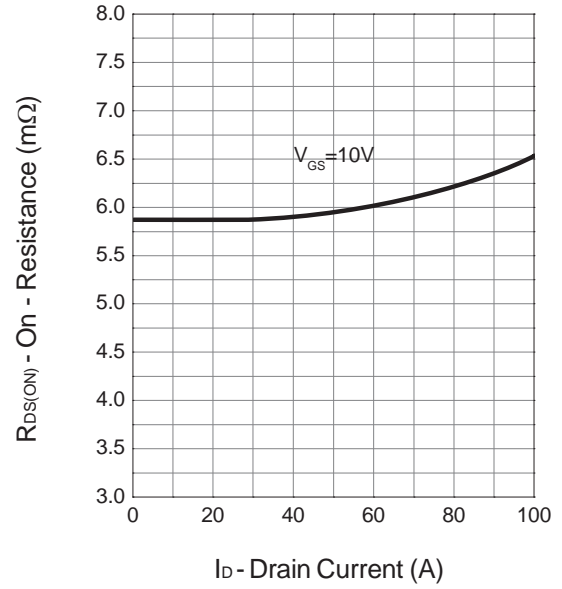


Typical Operating Characteristics (Cont.)

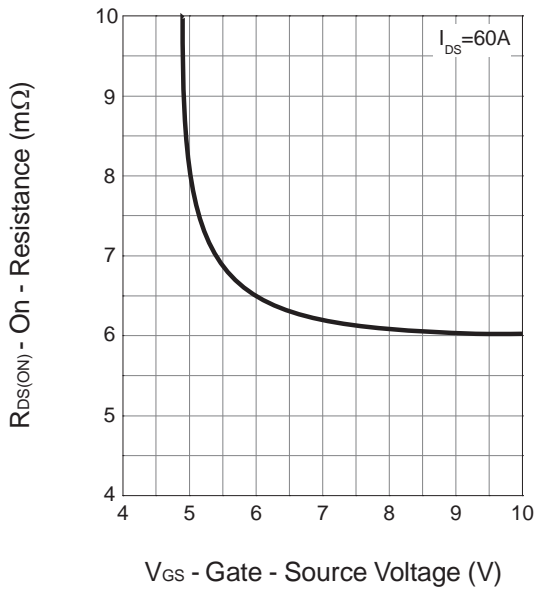
Output Characteristics



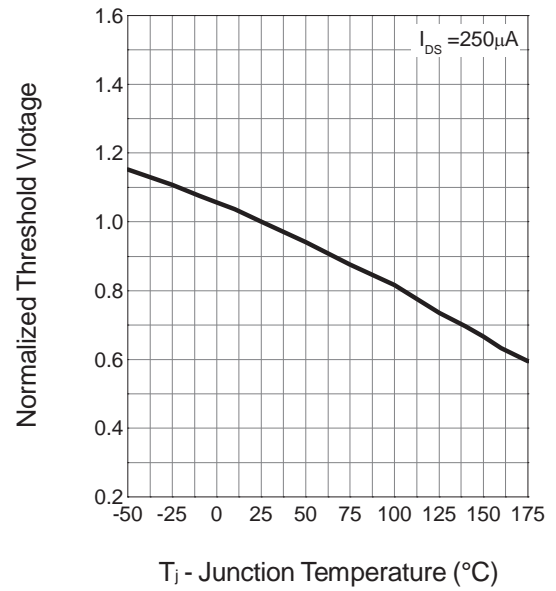
Drain-Source On Resistance



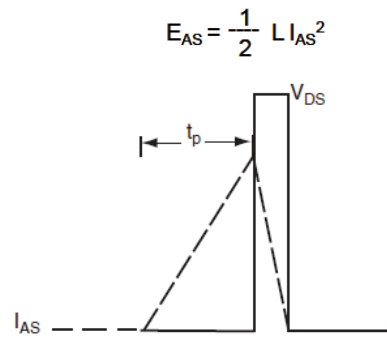
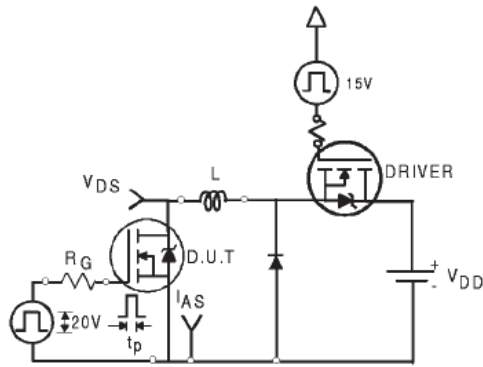
Drain-Source On Resistance



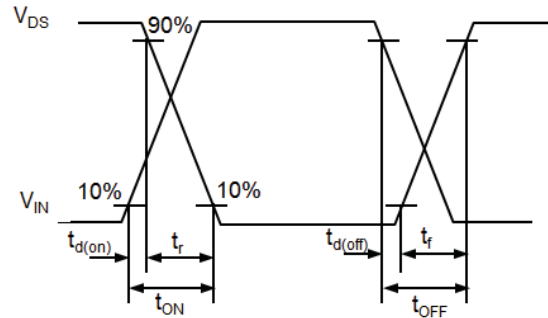
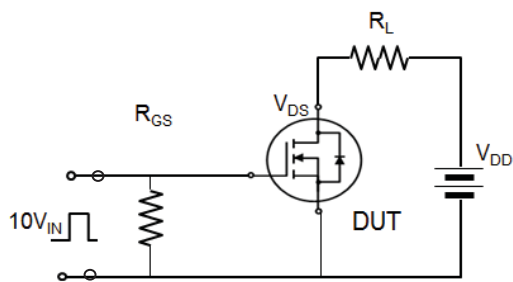
Gate Threshold Voltage



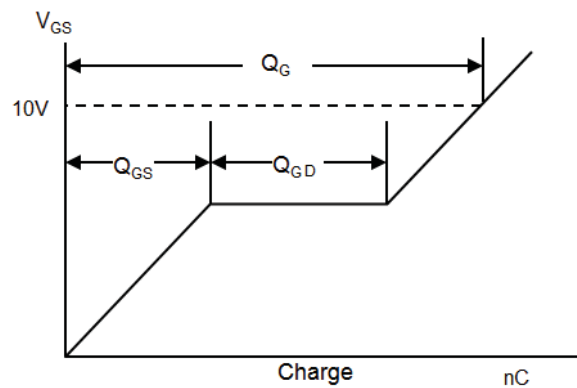
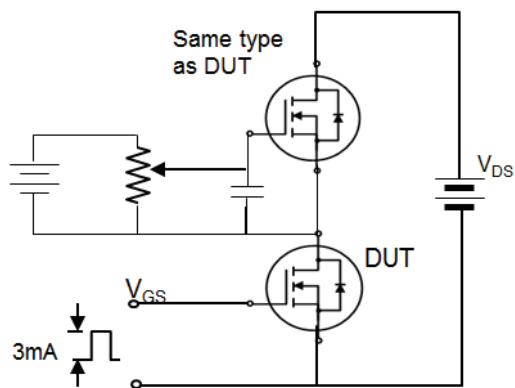
Avalanche Test Circuit



Switching Time Test Circuit



Gate Charge Test Circuit



3 DFNDJH, QIRUP DMRQ

72 \$%

&20021',0(16,216

6<0%2/	PP		
	0,1	120	0\$;
\$			
\$			
\$			
E			
E			
F			
'			
'			
'			
(
(
H	%6&		
H	%6&		
+			
/			
/			
- 3			
4			

3 DFNDJ H, QIRUP DMRQ

72

&20021',0(16,216

6<0%2/	PP		
	0,1	120	0\$;
\$			
\$			
\$			
\$			
E			
E			
F			
,			
,			
(
(
H	%6&		
+			
+			
/			
/			
/	%6&		
	<i>f</i>	<i>f</i>	<i>f</i>